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PTO/SB/08A (10-01)

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U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

<b>Substitute for form 1449A/PTO</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)			<b>Complete if Known</b>		
			Application Number	10/736,617	
			Filing Date	December 17, 2003	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	2825	
			Examiner Name	R. Rocchegiani	
Sheet	1	of	5	Attorney Docket Number	M4065.0698/P698-A

U.S. PATENT DOCUMENTS					
Exami ner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
V	**AA	2002/0072188	6/13/2002	Gilton	
	**AB	2002/0106849	08/08/2002	Moore	
	**AC	2002/0123169	09/05/2002	Moore et al.	
	**AH	2002/0123248	09/05/2002	Moore et al.	
	**AI	2002/0132417	09/09/2002	Li	
	**AJ	2002/0160551	10/31/2002	Harshfield	
	**AK	2002/0168852	11/14/2002	Harshfield et al.	
	**AL	2002/0190289	12/19/2002	Harshfield et al.	
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	**AM	2003/0043631	03/06/2003	Gilton et al.	
	**AN	2003/0045049	03/06/2003	Campbell et al.	
	**AO	2003/0045054	03/06/2003	Campbell et al.	
	**AP	2003/0047765	03/13/2003	Campbell	
	**AQ	2003/0047772	03/13/2003	Li	
	**AR	2003/0047773	03/13/2003	Li	
	**AS	2003/0048519	03/13/2003	Kozicki	
	**AT	2003/0048744	3/2003	Ovshinsky et al.	
	**AU	2003/0049912	03/13/2003	Campbell et al.	
	**AV	2003/0068861	04/10/2003	Li	
	**AW	2003/0068862	04/10/2003	Li	
	**AX	2003/0095426	05/22/2003	Hush et al.	
	**AY	2003/0096497	05/22/2003	Moore et al.	
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	**AA1	2003/0117831	06/26/2003	Hush	
	**AB1	2003/0128612	07/10/2003	Moore et al.	
	**AC1	2003/0137869	07/24/2003	Kozicki	
	**AD1	2003/0143782	07/31/2003	Gilton et al.	
	**AE1	2003/0155589	08/21/2003	Campbell et al.	
	**AF1	2003/0155606	08/21/2003	Campbell et al.	
	**AG1	2003/0156447	08/21/2003	Kozicki	
	**AH1	2003/0156463	08/21/2003	Casper et al.	
	**AI1	2003/0209728	11/13/2003	Kozicki et al.	
	**AJ1	2003/0209971	11/13/2003	Kozicki et al.	
	**AK1	2003/0210564	11/13/2003	Kozicki et al.	
	**AL1	2003/0212724	11/2003	Ovshinsky et al.	
	**AM1	2003/0212725	11/2003	Ovshinsky et al.	
	**AN1	2004/0035401	2/2004	Ramachandran et al.	
	**AO1	3,271,591	9/1966	Ovshinsky	
	**AP1	3,622,319	11/1971	Sharp	
	**AQ1	3,743,847	7/1973	Boland	
	**AR1	3,961,314	6/1976	Klose et al.	
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V	**AT1	3,983,542	11/1976	Ovshinsky	

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Sheet	2	of	5

✓	**AU1	3,988,720	10/1976	Ovshinsky	
↑	**AV1	4,177,474	12/1979	Ovshinsky	
	**AW1	4,267,261	5/1981	Hallman et al.	
	**AX1	4,269,935	5/1981	Masters et al.	
	**AY1	4,312,938	1/1982	Drexler, et al.	
	**AZ1	4,320,191	3/1982	Yoshikawa et al.	
	**AA2	4,405,710	9/1983	Balasubramanyam et al.	
	**AB2	4,499,557	2/1985	Holmberg et al.	
	**AC2	4,597,162	7/1986	Johnson et al.	
	**AD2	4,608,296	8/1986	Keem et al.	
	**AE2	4,637,895	1/1987	Ovshinsky et al.	
	**AF2	4,646,266	2/1987	Ovshinsky et al.	
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	**AH2	4,668,968	5/1987	Ovshinsky et al.	
	**AI2	4,670,763	6/1987	Ovshinsky et al.	
	**AJ2	4,673,957	6/1987	Ovshinsky et al.	
	**AK2	4,678,679	7/1987	Ovshinsky	
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	**AM2	4,698,234	10/1987	Ovshinsky et al.	
	**AN2	4,710,899	12/1987	Young et al.	
	**AO2	4,728,406	3/1988	Banerjee et al.	
	**AP2	4,737,379	4/1988	Hudgens et al.	
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	**AR2	4,769,338	9/1988	Ovshinsky et al.	
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	**AW2	4,818,717	4/1989	Johnson et al.	
	**AX2	4,843,443	6/1989	Ovshinsky et al.	
	**AY2	4,845,533	7/1989	Pryor et al.	
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	**AA3	4,853,785	8/1989	Ovshinsky et al.	
	**AB3	4,891,330	1/1990	Guha et al.	
	**AC3	5,128,099	7/1992	Strand et al.	
	**AD3	5,159,661	10/1992	Ovshinsky et al.	
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	**AF3	5,177,567	1/1993	Klersy et al.	
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	**AL3	5,341,328	8/1994	Ovshinsky et al.	
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	**AN3	5,359,205	10/1994	Ovshinsky	
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✓	**AP3	5,406,509	4/1995	Ovshinsky et al.	
✓	**AQ3	5,414,271	5/1995	Ovshinsky et al.	

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		Examiner Name	R. Rocchegiani
Sheet	3	of	5
		Attorney Docket Number	M4065.0698/P698-A

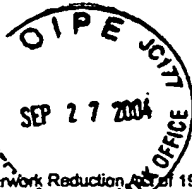
04	**AR3	5,512,328	4/1996	Yoshimura et al.	
↑	**AS3	5,512,773	4/1996	Wolf et al.	
	**AT3	5,534,711	7/1996	Ovshinsky et al.	
	**AU3	5,534,712	7/1996	Ovshinsky et al.	
	**AV3	5,536,947	7/1996	Klersy et al.	
	**AW3	5,543,737	8/1996	Ovshinsky	
	**AX3	5,591,501	1/1997	Ovshinsky et al.	
	**AY3	5,596,522	1/1997	Ovshinsky et al.	
	**AZ3	5,687,112	11/1997	Ovshinsky	
	**AA4	5,694,054	12/1997	Ovshinsky et al.	
	**AB4	5,714,768	2/1998	Ovshinsky et al.	
	**AC4	5,726,083	3/1998	Takaishi	
	**AD4	5,789,277	8/1998	Zahorik et al.	
	**AE4	5,814,527	9/29/1998	Wolstenholme et al	
	**AF4	5,818,749	10/06/1998	Harshfield	
	**AG4	5,825,046	10/1998	Czubatyj et al.	
	**AH4	5,841,150	11/1998	Gonzalez et al.	
	**AI4	5,846,889	12/1998	Harbison et al.	
	**AJ4	5,851,882	12/22/1998	Harshfield	
	**AK4	5,869,843	2/9/1999	Harshfield	
	**AL4	5,896,312	4/20/1999	Kozicki et al.	
	**AM4	5,912,839	6/1999	Ovshinsky et al.	
	**AN4	5,914,893	6/22/1999	Kozicki et al.	
	**AO4	5,933,365	8/1999	Klersy et al.	
	**AP4	5,998,066	12/1999	Block et al.	
	**AQ4	6,011,757	1/2000	Ovshinsky	
	**AR4	6,031,287	2/29/2000	Harshfield	
	**AS4	6,077,729	6/2000	Harshfield	
	**AT4	6,084,796	7/4/2000	Kozicki et al.	
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	**AB5	6,297,170	10/2001	Gabriel et al.	
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				Art Unit	2825
				Examiner Name	R. Rocchegiani
Sheet	4	of	5	Attorney Docket Number	M4065.0698/P698-A

✓	**AO5	6,423,628	7/2002	Li et al.	
✓	**AP5	6,429,064	8/2002	Wicker	
✓	**AQ5	6,437,383	8/2002	Xu	
✓	**AR5	6,440,837	8/27/2002	Harshfield	
✓	**AS5	6,462,984	10/2002	Xu et al.	
✓	**AT5	6,480,438	11/2002	Park	
✓	**AU5	6,487,113	11/2002	Park et al.	
✓	**AV5	6,501,111	12/2002	Lowery	
✓	**AW5	6,507,061	1/2003	Hudgens et al.	
✓	**AX5	6,511,862	1/2003	Hudgens et al.	
✓	**AY5	6,511,867	1/2003	Lowery et al.	
✓	**AZ5	6,512,241	1/2003	Lai	
✓	**AA6	6,514,805	2/2003	Xu et al.	
✓	**AB6	6,531,373	3/2003	Gill et al.	
✓	**AC6	6,534,781	3/2003	Dennison	
✓	**AD6	6,545,287	4/2003	Chiang	
✓	**AE6	6,545,907	4/2003	Lowery et al.	
✓	**AF6	6,555,860	4/2003	Lowery et al.	
✓	**AG6	6,563,164	5/2003	Lowery et al.	
✓	**AH6	6,566,700	5/2003	Xu	
✓	**AI6	6,567,293	5/2003	Lowery et al.	
✓	**AJ6	6,569,705	5/2003	Chiang et al.	
✓	**AK6	6,570,784	5/2003	Lowery	
✓	**AL6	6,576,921	6/2003	Lowery	
✓	**AM6	6,586,761	7/2003	Lowery	
✓	**AN6	6,589,714	7/2003	Maimon et al.	
✓	**AO6	6,590,807	7/2003	Lowery	
✓	**AP6	6,593,176	7/2003	Dennison	
✓	**AQ6	6,597,009	7/2003	Wicker	
✓	**AR6	6,605,527	8/2003	Dennison et al.	
✓	**AS6	6,613,604	9/2003	Maimon et al.	
✓	**AT6	6,621,095	9/2003	Chiang et al.	
✓	**AU6	6,625,054	9/2003	Lowery et al.	
✓	**AV6	6,638,820	10/2003	Moore	
✓	**AW6	6,642,102	11/2003	Xu	
✓	**AX6	6,646,297	11/2003	Dennison	
✓	**AY6	6,649,928	11/2003	Dennison	
✓	**AZ6	6,667,900	12/2003	Lowery et al.	
✓	**AA7	6,671,710	12/2003	Ovshinsky et al.	
✓	**AB7	6,673,648	1/2004	Lowrey	
✓	**AC7	6,673,700	1/2004	Dennison et al.	
✓	**AD7	6,674,115	1/2004	Hudgens et al.	
✓	**AE7	6,687,427	2/2004	Ramalingam et al.	
✓	**AF7	6,690,026	2/2004	Peterson	
✓	**AG7	6,696,355	2/2004	Dennison	
✓	**AH7	6,687,153	2/2004	Lowery	
✓	**AI7	6,707,712	3/2004	Lowery	
✓	**AJ7	6,714,954	3/2004	Ovshinsky et al.	



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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	To
		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)					
VY	**BA	JP 5-6126916		10/19981	Akira et al.		
VY	**BB	WO 00/48196		08/17/2000	Kozicki et al.		
VY	**BC	WO 02/21542		03/14/2002	Kozicki et al.		

Examiner Signature	V. Y. Rocchegiani	Date Considered	09/22/05
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Sheet	1	of	8		

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AD	6,487,106		11/26/2002	Kozicki		
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AF	2002/0190350 APP		12/19/2002	Kozicki		
AG	2003/0027416 APP		2/6/2003	Moore		
AH	2003/0001229 APP		1/2/2003	Moore et al.		
AI	2002/0127886 APP		9/12/2002	Moore et al.		
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AK	2002/0163828 APP		11/2002	Krieger et al.		
AL	6,072,716		6/2000	Jacobson et al.		
AM	5,272,359		12/93	Nagasubramanian et al.		
AN	4,671,618		6/87	Wu et al.		
AO	4,800,526		1/89	Lewis		
AP	2003/0035314		02/20/03	Kozicki		
AQ	2003/0035315		02/20/03	Kozicki		
AR	US 2002/0168820		11/14/2002	Kozicki et al.		
AS	6,469,364		10/22/2002	Kozicki		
AT	6,388,324		05/14/2002	Kozicki et al.		
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VY	BA	WO 97/48032	12/18/1997	Kozicki et al.		
VY	BB	WO 99/28914	06/10/1999	Kozicki et al.		

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VY	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
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09/22/05

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09/22/05

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				Filing Date	December 12, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	8	of	8	Attorney Docket Number	M4065.0698/P698-A

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